

a printed wiring substrate having a plurality of wiring layers;
a thermal expansion buffering sheet integrally laminated on a surface of
said printed wiring substrate and having a lower coefficient of thermal expansion
than that of said printed wiring substrate; and
a semiconductor device provided on the thermal expansion buffering
sheet,

wherein the thermal expansion buffering sheet has a higher coefficient of
thermal expansion than the semiconductor device.

2. A printed wiring board according to claim 1, wherein a coefficient
of thermal expansion of said printed wiring substrate is 13 to 20 ppm, and a
coefficient of thermal expansion of said thermal expansion buffering sheet is 6
to 12 ppm.

3. A printed wiring board according to claim 1, wherein said printed
wiring substrate is a multi-layer wiring board which laminates wiring layers and
insulation layers which are made of a glass cloth impregnated with an epoxy
resin, alternately.

4. A printed wiring board according to claim 1, wherein said thermal
expansion buffering sheet is made of an aramid.

5. (Amended) A printed wiring board according to claim 1, further
comprising an electrode pattern on a surface of said thermal expansion buffering
sheet connecting the semiconductor device to a wiring section of said printed
wiring board.

6. (Amended) A printed wiring board according to claim 5, wherein the
semiconductor device is connected to said electrode pattern via a solder ball.

7. (Amended) A printed wiring board comprising:

a multi-layer wiring section which laminates wiring layers and insulation layers alternately;

a thermal expansion buffering sheet integrally laminated on a surface of said multi-layer wiring section and having a lower coefficient of thermal expansion than that of said multi-layer wiring section; and

a semiconductor device provided on the thermal expansion buffering sheet,

wherein the thermal expansion buffering sheet has a higher coefficient of thermal expansion than the semiconductor device.

8. (Amended) A printed wiring board comprising:

a multi-layer wiring section which laminates wiring layers and insulation layers alternately;

a thermal expansion buffering sheet integrally laminated on a surface of said multi-layer wiring section and having a lower coefficient of thermal expansion than that of said multi-layer wiring section;

a semiconductor device provided on the thermal expansion buffering sheet; and

an electrode pattern provided on a surface of said thermal expansion buffering sheet connecting the semiconductor device to the multi-layer wiring section,

wherein the thermal expansion buffering sheet has a higher coefficient of thermal expansion than the semiconductor device.

9. (Amended) A printed wiring board comprising:

a multi-layer wiring section which laminates wiring layers and insulation layers alternately;

a thermal expansion buffering sheet, a material of which is aramid, integrally laminated on a surface of said multi-layer wiring section and having a lower coefficient of thermal expansion than that of said multi-layer wiring section; and

a semiconductor device provided on the thermal expansion buffering sheet,

wherein the thermal expansion buffering sheet has a higher coefficient of thermal expansion than the semiconductor device.

10. (Amended) A printed wiring board comprising:
a multi-layer wiring section which laminates wiring layers and insulation layers alternately;

a thermal expansion buffering sheet, a material of which is aramid, integrally laminated on a surface of said multi-layer wiring section and having a lower coefficient of thermal expansion than that of said multi-layer wiring section;

a semiconductor device provided on the thermal expansion buffering sheet; and

an electrode pattern provided on a surface of said thermal expansion buffering sheet connecting the semiconductor device to the multi-layer wiring section,

wherein the thermal expansion buffering sheet has a higher coefficient of thermal expansion than the semiconductor device.